



Stud Diode

Rectifier Diode

SKN 26
SKR 26

Features

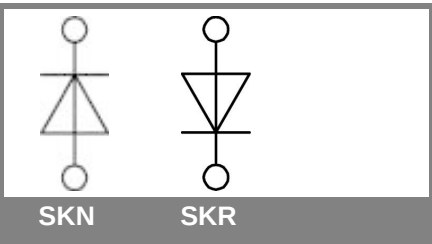
- Reverse voltages up to 1600 V
- Hermetic metal case with glass insulator
- Threaded stud ISO M6 (SKR 26 also 10 - 32 UNF)
- SKN: anode to stud, SKR: cathode to stud

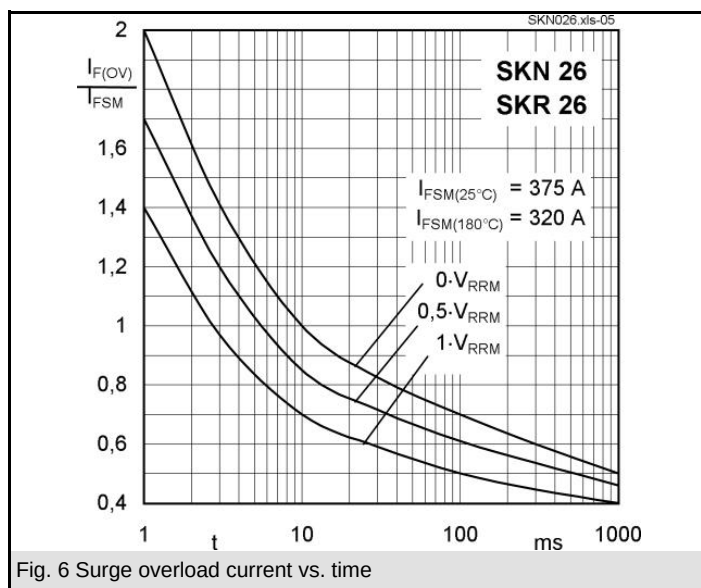
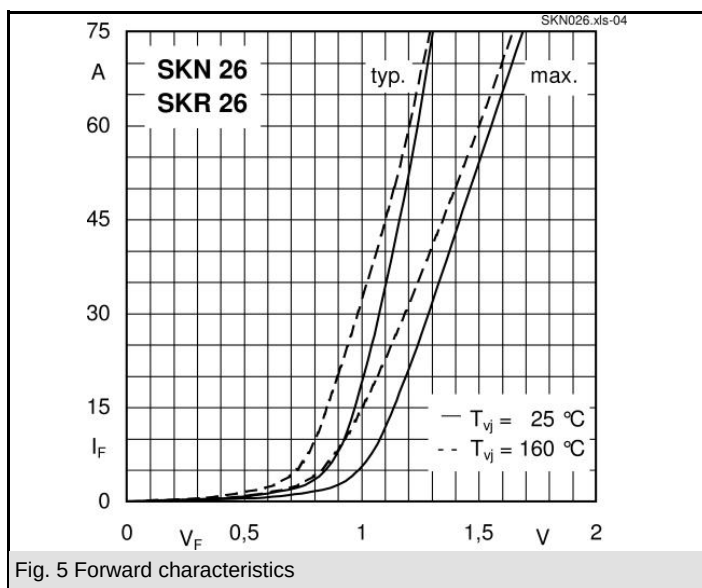
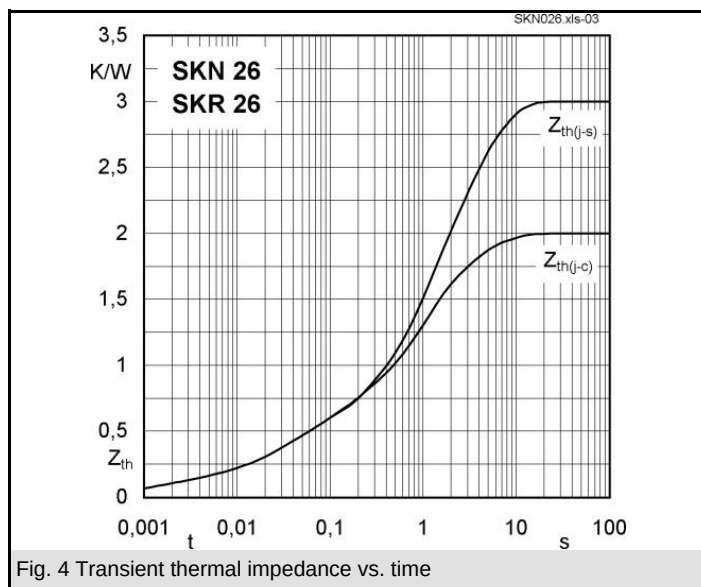
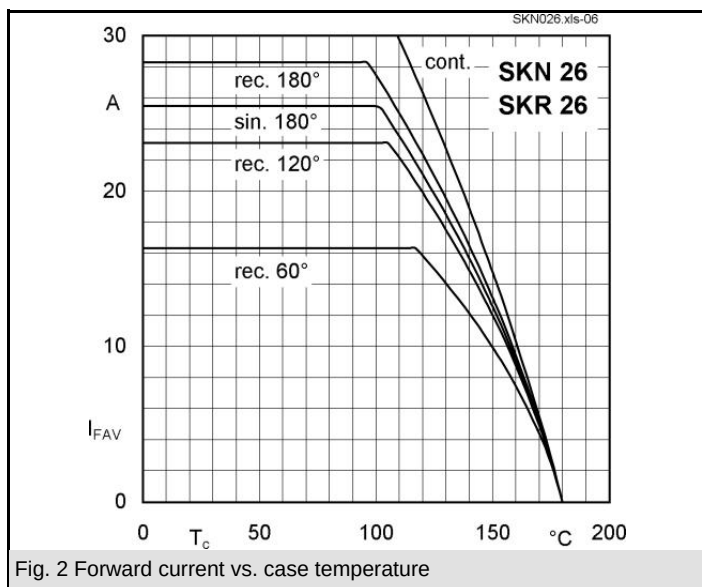
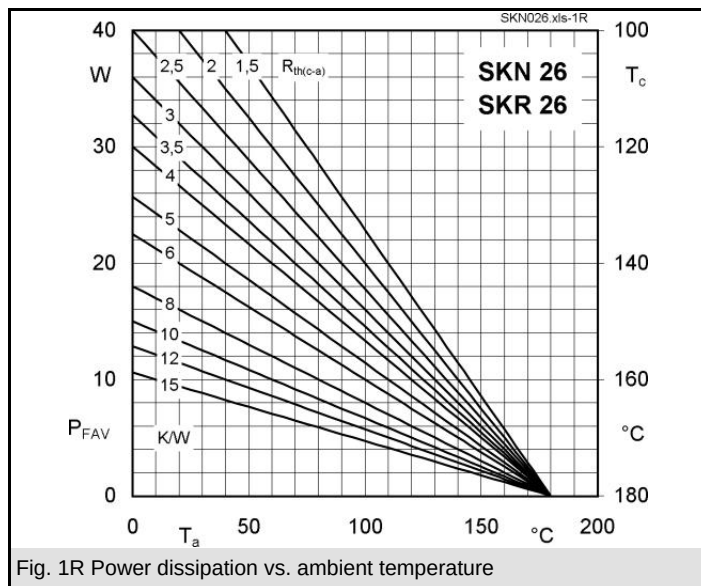
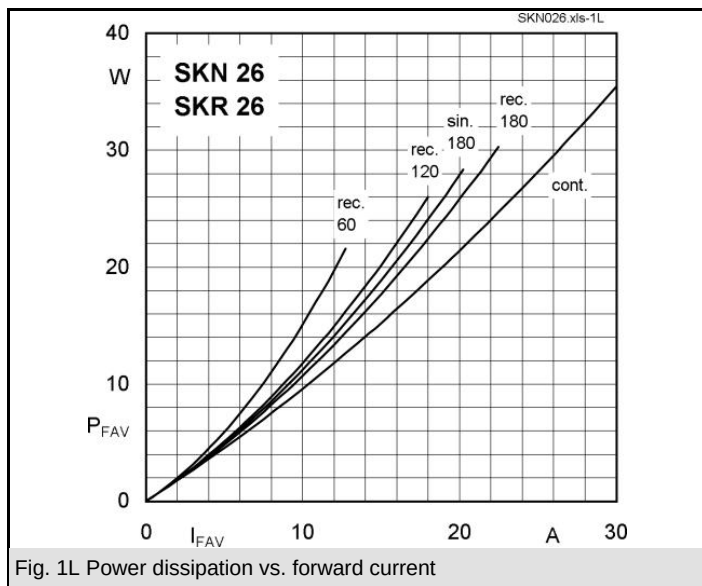
Typical Applications*

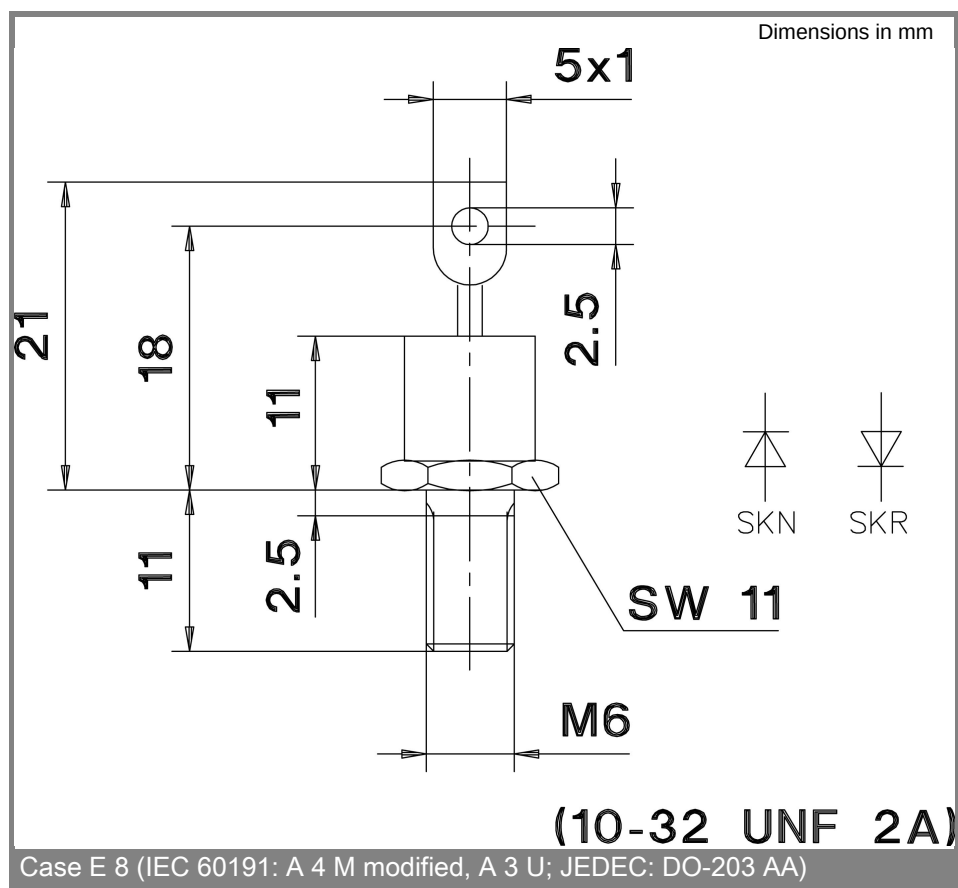
- All-purpose mean power rectifier diodes
- Cooling via metal plates or heatsinks
- Non-controllable and half-controllable rectifiers
- Free-wheeling diodes
- Recommended snubber network:
RC: 0,05 µF, 200 Ω (P_R = 1 W),
R_P = 150 kΩ (P_R = 4 W)

V _{RSM} V	V _{RRM} V	I _{FRMS} = 40 A (maximum value for continuous operation)		
		I _{FAV} = 25 A (sin. 180 °; T _c = 100 °C)		
400	400	SKN 26/04	SKR 26/04	
800	800	SKN 26/08	SKR 26/08	
1200	1200	SKN 26/12	SKR 26/12	
1400	1400	SKN 26/14	SKR 26/14	
1600	1600	SKN 26/16	SKR 26/16	

Symbol	Conditions	Values	Units
I _{FAV}	sin. 180; T _c = 100 °C	25	A
I _D	K 9; T _a = 45 °C; B2 / B6	20 / 29	A
	K 3; T _a = 45 °C; B2 / B6	35 / 50	A
I _{FSM}	T _{vj} = 25 °C; 10 ms	375	A
	T _{vj} = 180 °C; 10 ms	320	A
i ² t	T _{vj} = 25 °C; 8,3 ... 10 ms	700	A²s
	T _{vj} = 180 °C; 8,3 ... 10 ms	510	A²s
V _F	T _{vj} = 25 °C; I _F = 60 A	max. 1,55	V
V _(TO)	T _{vj} = 180 °C	max. 0,85	V
r _T	T _{vj} = 180 °C	max. 11	mΩ
I _{RD}	T _{vj} = 180 °C; V _{RD} = V _{RRM}	max. 4	mA
Q _{rr}	T _{vj} = 160 °C; - di _F /dt = 10 A/µs	20	µC
R _{th(j-c)}		2	K/W
R _{th(c-s)}		1	K/W
T _{vj}		- 40 ... + 180	°C
T _{stg}		- 55 ... + 180	°C
V _{isol}		-	V~
M _s	to heatsink	2,0	Nm
a		5 * 9,81	m/s²
m	approx.	7	g
Case		E 8	







* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.